# SHINDENGEN

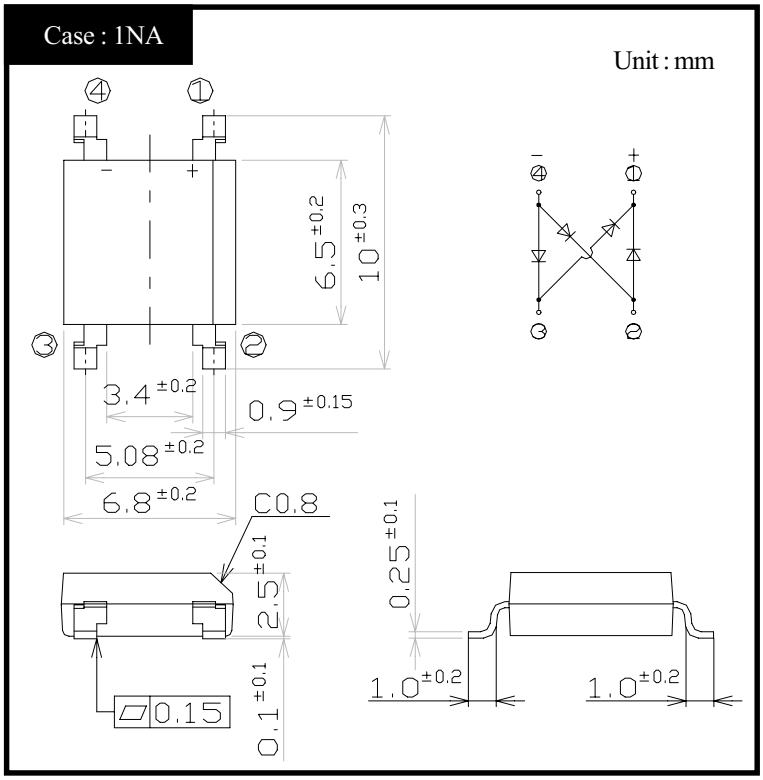
## General Purpose Rectifiers

**SMT Bridges**

# S1NBB80

**800V 1A**

## OUTLINE DIMENSIONS




## RATINGS

Absolute Maximum Ratings (If not specified Ta=25℃)

| Item | Symbol | Conditions | Ratings | Unit |
|---|---|---|---|---|
| Storage Temperature | Tstg | | -40 to 150 | ℃ |
| Operating Junction Temperature | Tj | | 150 | ℃ |
| Maximum Reverse Voltage | $V_{RM}$ | | 800 | V |
| Average Rectified Forward Current | Io | 50Hz sine wave, R-load, Glass-epoxy substrate, Ta=26℃ *1 | 1 | A |
| | Io | 50Hz sine wave, R-load, Glass-epoxy substrate, Ta=25℃ *2 | 0.84 | A |
| Peak Surge Forward Current | $I_{FSM}$ | 50Hz sine wave, Non-repetitive 1 cycle peak value, Tj=25℃ | 50 | A |
| Current Squared Time | $I^2t$ | 1ms≦t＜10ms Tj=25℃ | 6 | $A^2s$ |

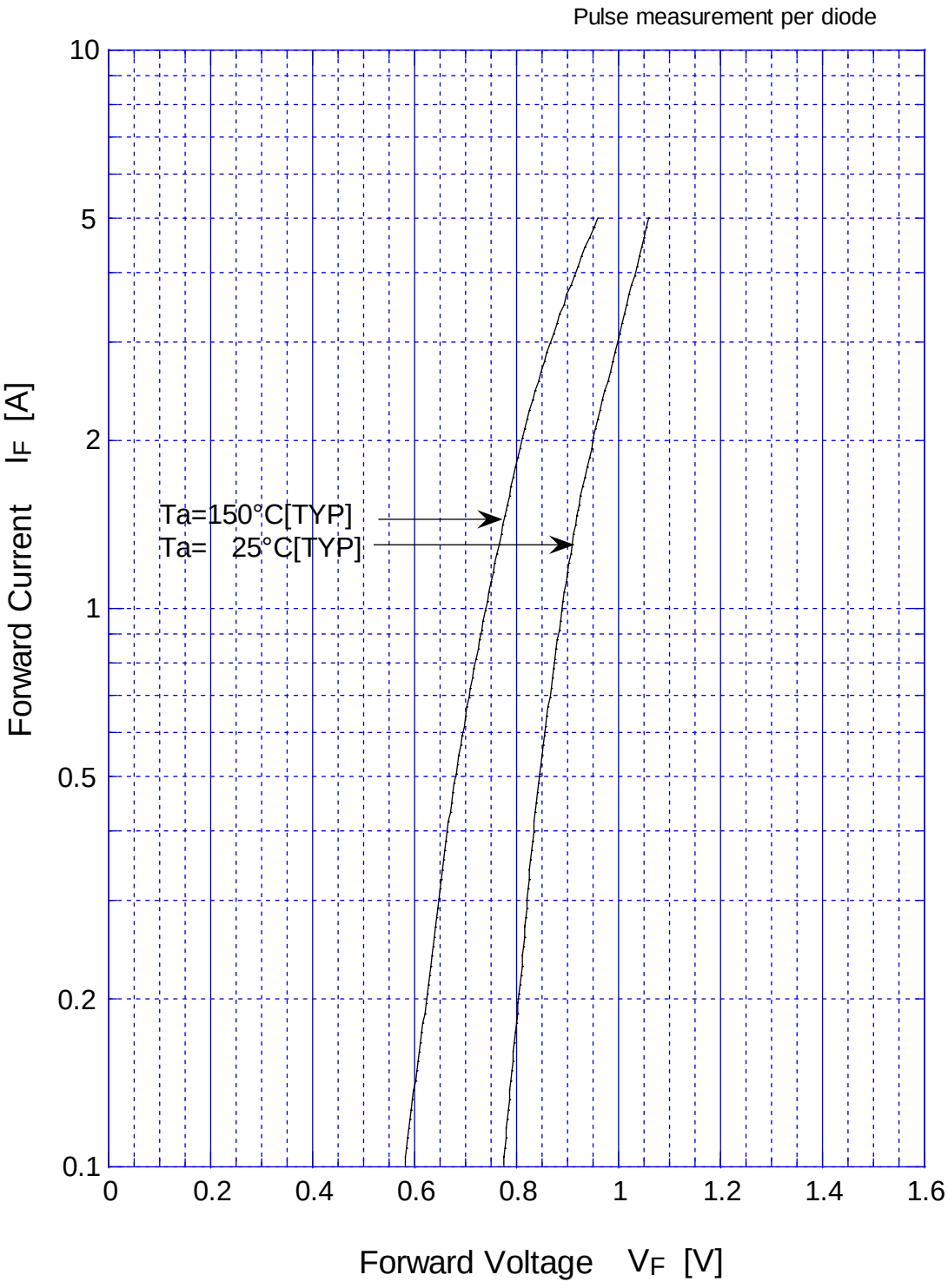
Electrical Characteristics (If not specified Ta=25℃)

| Item | Symbol | Conditions | Ratings | Unit |
|---|---|---|---|---|
| Forward Voltage | $V_F$ | $I_F$=0.5A, Pulse measurement, Rating of per diode | Max 1.05 | V |
| Reverse Current | $I_R$ | $V_R$=$V_{RM}$, Pulse measurement, Rating of per diode | Max 10 | μA |
| Thermal Resistance | θjl | junction to lead | Max 15 | ℃/W |
| | θja | junction to ambient *1 | Max 68 | |
| | θja | junction to ambient *2 | Max 84 | |

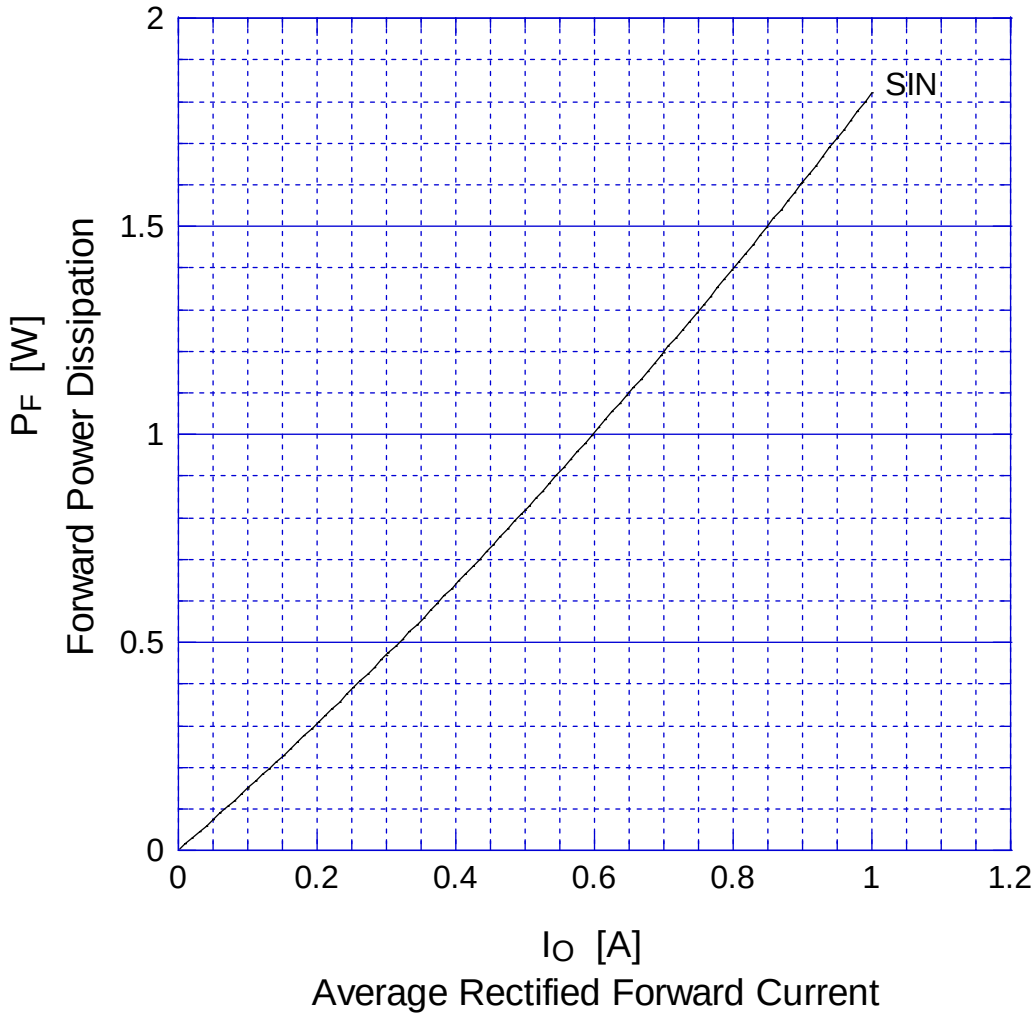
*1 : Glass epoxy substrate (pattern area : 324$mm^2$)

*2 : Glass epoxy substrate (pattern area : 101$mm^2$)

# S1NBB80 Forward Voltage

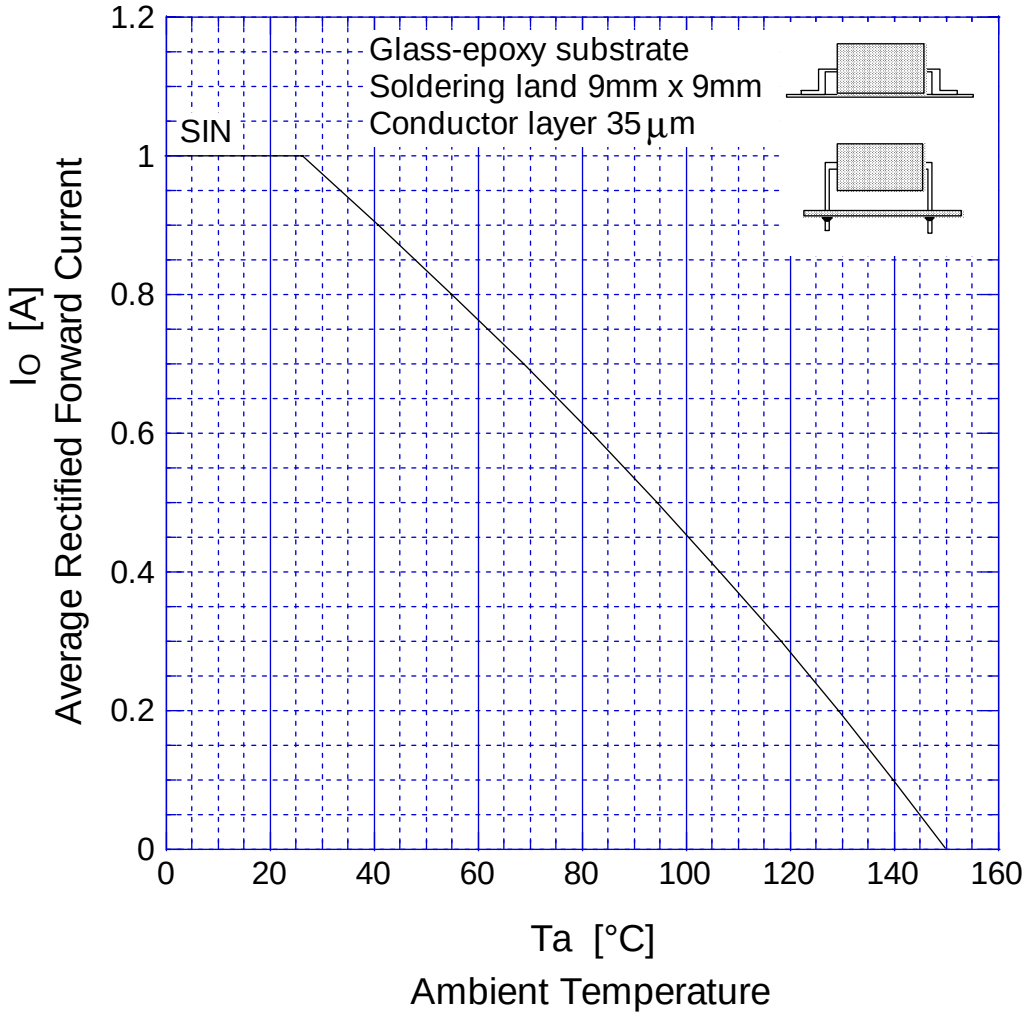


# S1NBB80 Forward Power Dissipation




Tj = 150°C

# S1NBB80 Derating Curve




$V_R = V_{RM}$

# S1NBB80 Peak Surge Forward Capability